

REMARKS

Claim 45 is amended. Claims 45-52 are pending in the application.

Claims 45 and 48-50 stand rejected under 35 U.S.C. §102 as being anticipated either of Yuan U.S. Patent No. 5,534,456; and Yu U.S. Patent No. 6,180,468. The Examiner is reminded by direction to MPEP §2131 that anticipation requires each individual element of a claim to be disclosed in a single prior art reference. Claims 45 and 48-50 are allowable over each of Yuan and Yu for at least the reason that neither of the references discloses each and every element in any of those claims.

As amended, independent claim 45 recites forming a coating over a pair of adjacent blocks and across a first gap between the adjacent blocks, and selectively removing the coating from across the first gap while leaving the coating along sidewalls and elevationally over the pair of adjacent blocks. Claim 45 further recites implanting at least one dopant within semiconductive material while the enlarged blocks remain over the semiconductive substrate material. The amendment to claim 45 is supported by the specification at, for example, Figs. 4-6, and the text at paragraphs 70 and 73-75. Yuan discloses narrowing openings within an oxide layer by depositing a layer of silicon dioxide and anisotropically etching the silicon dioxide layer to leave only portions of the oxide layer adjacent sidewalls in the form of spacers 19 (Figs. 3 and 4, and Col. 6, lines 40-50). Yu discloses formation of nitride gate spacers 32 and 34, followed by dopant implantation (Fig. 4 and Col. 3, lines 30-41). Neither Yuan nor Yu discloses the claim 45 recited selectively removing a coating from across a first gap while leaving coating along sidewalls and elevationally over a pair of adjacent blocks, and implanting at least one dopant while the enlarged blocks remain on the semiconductive substrate material. Accordingly, claim 45 is not anticipated by either

Yuan or Yu. Further, neither Yuan nor Yu suggests the recited leaving coating along sidewalls and elevationally over a pair of adjacent blocks, and implanting at least one dopant while the enlarged blocks remain over the semiconductive substrate material. Claim 45 is, therefore, not rendered obvious by Yuan or Yu.

Dependent claims 48-50 are allowable over each of Yuan and Yu for at least the reason that they depend from allowable base claim 45.

Claims 46 and 47 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Yuan, as combined with DeJule "Paths to Smaller Features" (website). The Examiner is reminded by direction to MPEP §2143 that a proper obviousness rejection has the following three requirements: 1) there must be some suggestion or motivation to modify or combine reference teachings; 2) there must be a reasonable expectation of success; and 3) the combined references must teach or suggest all of the claim limitations. Claims 46 and 47 are allowable over Yuan in combination with DeJule for at least the reason that the references, individually or as combined, fail to disclose or suggest each and every limitation in any of those claims.

As indicated above, Yuan does not disclose or suggest that claim 45 recited selectively removing coating from across a first gap while leaving the coating along sidewalls and elevationally over a pair of adjacent blocks, and implanting at least one dopant while the enlarged blocks remain over the semiconductive substrate material. As indicated at page 6 of the present Action, DeJule is relied upon as disclosing utilization of a coating material which cross-links. However, the coating material disclosed by DeJule does not contribute towards suggesting the claim 45 recited selectively removing coating from across a first gap while leaving coating along sidewalls and elevationally over a pair of

adjacent blocks, and implanting dopant while the enlarged blocks remain over the semiconductive substrate material. Accordingly, claim 45 is not rendered obvious by the combination of Yuan and DeJule. Dependent claims 46 and 47 are allowable over Yuan and DeJule for at least the reason that they depend from allowable base claim 45.

Claims 45 and 50-52 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Iwamatsu U.S. Patent No. 5,440,161, as combined with Yu. As discussed above, Yu does not disclose or suggest the claim 45 recited selectively removing coating from across a first gap while leaving coating along sidewalls and elevationally over a pair of adjacent blocks, and implanting at least one dopant within the semiconductive material while the enlarged blocks remain over the semiconductive substrate material. As indicated at page 6-7 of the present Action, Iwamatsu is relied upon as disclosing isolation gate formation. As acknowledged by the Examiner at page 7 in the present Action, Iwamatsu does not disclose or suggest, or contribute towards suggesting formation of patterned blocks separated by a gap, forming a coating over a pair of adjacent blocks, selectively removing coating, or implanting at least one dopant while the enlarged blocks are over semiconductive substrate material. Accordingly, as combined with Yu, Iwamatsu does not contribute towards suggesting the claim 45 recited selectively removing coating from across a first gap while leaving coating along sidewalls and elevationally over a pair of adjacent blocks, and while the enlarged blocks remain over the substrate material implanting at least one dopant within the gap. Accordingly, independent claim 45 is not rendered obvious by the combination of Iwamatsu and Yu, and is allowable over these references.

Dependent claims 50-52 are allowable over decided combination of Iwamatsu and Yu for at least the reason that they depend from allowable base claim 45.

For the reasons discussed above, claims 45-52 are allowable. Accordingly, applicant respectfully requests formal allowance of such claims in the Examiner's next action.

Respectfully submitted,

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